

Green Products

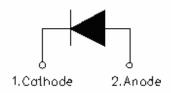
MURF860 ULTRAFAST PLASTIC RECTIFIER

Applications:

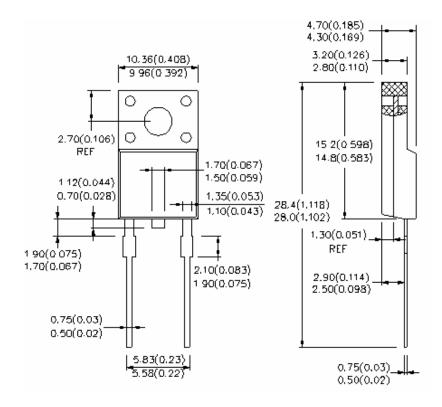
- Switching Power Supply
- Power Switching Circuits
- General Purpose

Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request



Mechanical Dimensions: In Inches / mm



ITO-220AC

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Marking Diagram:



Where XXXXX is YYWWL

MUR = Device Type F = Package type

8 = Forward Current (8A) 60 = Reverse Voltage (600V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping	
MURF860	ITO-220AC	50pcs / tube	
	(Pb-Free)	Sopes / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MURF860	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	420	V
Average Rectified Output Current @T _A = 55°C	lo	8.0	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	110	А
Forward Voltage (per element) @I _F = 8.0A, T _J =25°C	V_{FM1}	2.2	V
@I _F = 8.0A, T _J =100°C	V_{FM2}	2.0	V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5 50	μA
Maximum Reverse Recovery Time (Note 1)	Trr	50	ns
Max. Voltage Rate of Change	dv/dt	10,000	V/µs
Typical Thermal Resistance Junction to Ambient (Note 2)	$R_{ heta JA}$	25	K/W
Storage Temperature Range	$T_{STG_{i}}T_{J}$	-55 to +150	°C
Approximate Weight	wt	1.6	g
Case Style	ITO-220AC		

Note: 1. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

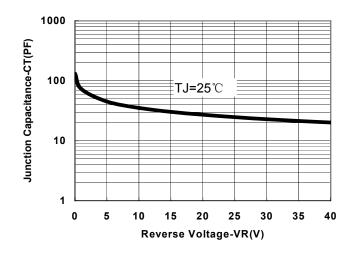
^{2.} Mount on Cu-Pad Size 16mm×16mm on P.C.B.

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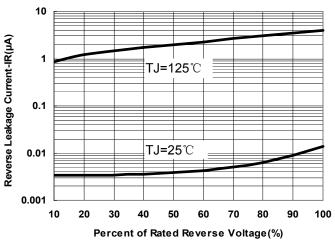


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

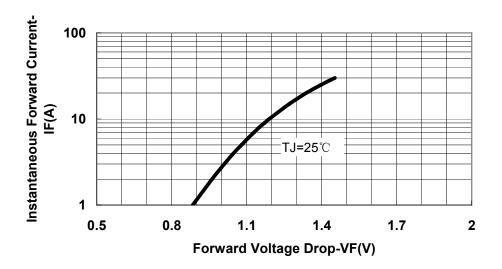


Fig.3-Typical Forward Voltage Drop Characteristics

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